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|  | <h2 style="color: #E67E22;">IPD70N10S3L-12</h2> | |
| | Hersteller-Teilenummer: | IPD70N10S3L-12 |
|  | Hersteller / Marke: | International Rectifier (Infineon Technologies) |
| | Teil der Beschreibung: | IPD70N10S3L-12 Infineon Technologies |
| Datenblätter: |  IPD70N10S3L-12.pdf | |
| RoHs Status: | Bleifrei / RoHS-konform | |
| Lagerzustand: | New original, 5981 pcs Stock Available. | |
| Liefern von: | Hong Kong | |
| Versandweg: | DHL/Fedex/TNT/UPS/EMS | |
| Image may be representation. See specs for product details. | | |

Spezifikationen

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|---|--|
| Teilenummer | IPD70N10S3L-12 |
| Hersteller | International Rectifier (Infineon Technologies) |
| Beschreibung | IPD70N10S3L-12 Infineon Technologies |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 5981 pcs Stock |
| Serie | OptiMOS™ |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 175°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-252-3, DPak (2 Leads + Tab), SC-63 |
| Supplier Device-Gehäuse | PG-TO252-3 |
| Verlustleistung (max) | 125W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 100V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 70A (Tc) |
| Rds On (Max) @ Id, Vgs | 11.5 mOhm @ 70A, 10V |
| VGS (th) (Max) @ Id | 2.4V @ 83µA |
| Gate Charge (Qg) (Max) @ Vgs | 77nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 5550pF @ 25V |
| Verpackung | Original-Reel® |

IPD70N10S3L-12 ist neu im Original, Suche IPD70N10S3L-12 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie IPD70N10S3L-12 International Rectifier (Infineon Technologies) mit Garantie und Vertrauen. Anfrage IPD70N10S3L-12: Info@Y-IC.com

Sie können auch interessiert sein:

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|---|--|---|--|
|  <p>IPD70P04P4-09 Original IPD70P04P4-09 Original</p> |  <p>IPD70N04S3-07 International Rectifier (Infineon Technologies) MOSFET N-CH 40V 82A TO252-3</p> |  <p>IPD70N12S3L12ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CHANNEL_100+</p> |  <p>IPD70N10S312ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 100V 70A TO252-3</p> |
|  <p>IPD70N10S3L12ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 100V 70A TO252-3</p> |  <p>IPD70N03S4L04ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 30V 70A TO252-3</p> |  <p>IPD70N10S3-12 VBsemi IPD70N10S3-12 VBsemi</p> |  <p>IPD70N03S4L04XT INFINEON IPD70N03S4L04XT INFINEON</p> |

heiße Teile

Mehr

- | | | | | |
|-----------------|------------------|-------------------|------------------|------------------|
| ⊗ IPD60R600C6 | ↔ IPD60R600CP | ⇒ IPD60R600E6 | D IPD60R600P6 | ↔ IPD60R750E6 |
| ⊣ IPD60R800CE | ⊗ IPD60R950C6 | D IPD640N06LG | ⇒ IPD64CN10NG | ↔ IPD65R1K4C6 |
| ⊗ IPD65R250C6 | ⊣ IPD65R250E6 | ⊗ IPD65R380C6 | ↔ IPD65R380E6 | ↔ IPD65R420CFD |
| D IPD65R420CFDA | ⊗ IPD65R600C6 | ⊣ IPD65R600E6 | ⊗ IPD65R660CFD | ↔ IPD65R950C6 |
| ⇒ IPD65R950CFD | ↔ IPD70N03S4L-04 | ⊗ IPD70N03S4L04XT | ⊣ IPD70N04S3-07 | ↔ IPD70N10S3-12 |
| ↔ IPD70P04P4-09 | ⇒ IPD70P04P4L-08 | D IPD75N04S4-06 | ⊗ IPD78CN10NG | ⊣ IPD800N06NG |
| ⊗ IPD80N04S3-06 | D IPD80N04S3-06B | ⇒ IPD80N06S3-09 | ↔ IPD80P03P4L-07 | ↔ IPD80R1K0CE |
| ⊣ IPD80R1K4CE | ⊗ IPD85P04P4L-06 | ↔ IPD90N03S4L-02 | ⇒ IPD90N03S4L-03 | ↔ IPD90N04S03-04 |
| ⊗ IPD90N04S3-04 | ⊣ IPD90N04S3-H4 | ⊗ IPD90N04S4-02 | D IPD90N04S4-03 | ↔ IPD90N04S4-04 |
| ↔ IPD90N04S4-05 | ⊗ IPD90N04S4L-04 | ⊣ IPD90N06S3-06 | ⊗ IPD90N06S3L-07 | ↔ IPD90N06S4-04 |

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